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LIGHT EMITTING DEVICE

Abstract

A light emitting device includes semiconductor laser elements, a frame part, one or more light-reflective members, wires, and one or more protective elements. One or more light-reflective members are configured to reflect laser light traveling from the semiconductor laser elements toward a first inner lateral surface of the frame part. The wires are not bonded to an upper surface of the frame part on a light traveling side beyond a virtual line coinciding with a side defining an upper edge of a light-reflective surface of the light-reflective member. A first protective element is arranged in the first region. A first wire is bonded to an upper surface of the frame part in a first region at a position on the light traveling side of the first protective element, and a second wire is bonded in the first region at a position on an element-side of the first protective element.

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Background/Summary

CROSS-REFERENCE TO RELATED APPLICATIONS [0001] This application is a continuation application of U.S. patent application Ser. No. 18/600,738, filed on Mar. 10, 2024, which is a continuation application of U.S. patent application Ser. No. 17/942,922, filed on Sep. 12, 2022, now U.S. Pat. No. 11,984,698, which is a continuation application of U.S. patent application Ser. No. 16/748,246, filed on Jan. 21, 2020, now U.S. Pat. No. 11,476,638. This application claims priority to Japanese Patent Application No. 2019-008494 filed on Jan. 22, 2019. The entire disclosures of U.S. patents application Ser. Nos. 18/600,738, 17/942,922 and 16/748,246 and Japanese Patent Application No. 2019-008494 are hereby incorporated herein by reference.

BACKGROUND

1. Technical Field

[0002] The present disclosure relates to a light emitting device.

2. Description of Related Art

[0003] Japanese published unexamined application No. 2011-254080 discloses a light emitting element package which includes a bottom part where a light emitting element is disposed, and a step provided at the periphery of the light emitting element. No. 2011-254080 also discloses that a bonding region is provided at the upper surface of the step, and a wire is bonded to the bonding region and to the light emitting element to electrically connect them. Japanese published unexamined application No. 2011-254080 also discloses that a Zener diode is provided at the upper surface of the step. In the light emitting element package, one cavity is provided for each light emitting element. Therefore, the size of the bonding region increases proportionally to the number of the light emitting elements.

[0004] There is still susceptible to improvement of the wiring pattern in a light emitting device including a plurality of light emitting elements.

SUMMARY

[0005] The present disclosure includes the following aspects.

[0006] A light emitting device includes a plurality of semiconductor laser elements, a frame part, one or more light-reflective members, a plurality of wires, and one or more protective elements. The frame part surrounds a bottom surface on which the semiconductor laser elements are disposed. The frame part has a pair of first inner lateral surfaces facing each other and a second inner lateral surface intersecting at least one of the first inner lateral surfaces. One or more light-reflective members are disposed on the bottom surface inside of the frame part, and configured to reflect laser light traveling from the semiconductor laser elements toward one of the first inner lateral surfaces of the frame part. The wires electrically connect the semiconductor laser elements. One or more protective elements include a first protective element. The wires are not bonded to an

upper surface of the frame part on a light traveling side beyond a virtual line coinciding with a side defining an upper edge of a light-reflective surface of the light-reflective member. The wires include a first wire and a second wire that are bonded to the upper surface of the frame part in a first region extending along the second inner lateral surface. The first protective element is arranged in the first region. The first wire is bonded to the upper surface of the frame part in the first region at a position on the light traveling side of the first protective element, and the second wire is bonded to the upper surface of the frame part in the first region at a position on an element-side of the first protective element.

[0007] The present disclosure realizes, in a light emitting device including a plurality of light emitting elements disposed at one surface, a suitable wiring pattern electrically connected to the plurality of light emitting elements.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0008] FIG. 1 is a perspective view of a light emitting device according to a first embodiment.

[0009] FIG. 2 is a top view of the light emitting device according to the first embodiment.

[0010] FIG. 3 is a perspective view for describing the inside configuration of the light emitting device according to the first embodiment.

[0011] FIG. 4 is a top view for describing the inside configuration of the light emitting device according to the first embodiment.

[0012] FIG. 5 is a top view of a base of the light emitting device according to the first embodiment.

[0013] FIG. 6 is a cross-sectional view of the light emitting device taken along line VI-VI in FIG. 2.

[0014] FIG. 7 is a top view of a light emitting device according to a modified example in which protective elements are connected with wires.

DETAILED DESCRIPTION OF EMBODIMENTS

[0015] In the description and the claims, the terms referring to any polygon such as a triangle, a quadrangle and the like include polygons having their corners (ends of sides) rounded, chamfered, beveled, or bowed. Similarly, any polygon having its side or sides deformed at an intermediate portion or intermediate portions is also referred to as a polygon. That is, any shape obtained by deforming a polygon is construed as “a polygon” recited in the description and the claims.

[0016] Without being limited to polygons, the same holds true for terms referring to a particular shape such as a trapezoid, a circle, or a recess or a projection. The foregoing also applies to each side forming such a shape. That is, a side which is deformed at its end or intermediate portion is still construed as “a side”. Note that, “a polygon” or “a side” without any intended deformation is referred to with the term “exact”, such as “an exact quadrangle”, when distinguished from any intentionally deformed shape.

[0017] In the following, with reference to the drawings, a description will be given of an embodiment for carrying out the present disclosure. While the embodiment embodies the technical idea of the present disclosure, it is not intended to limit the present disclosure. In the following description, identical names and reference characters are allotted to identical or similar members, and any repetitive description may be avoided as appropriate. The size or positional relationship of members in the drawings may be exaggerated for the sake of clarity.

First Embodiment

[0018] FIG. 1 is a perspective view of a light emitting device 1 according to a first embodiment.

FIG. 2 is a top view of the light emitting device 1 shown in FIG. 1. FIG. 3 is a perspective view for describing the inside configuration of the light emitting device 1, excluding a lid member 80. FIG. 4 is a top view of the light emitting device 1 shown in FIG. 3. FIG. 5 is a top view of just a base 10

of the light emitting device **1**. FIG. **6** is a cross-sectional view of the light emitting device **1** taken along line VI-VI in FIG. **2**.

[0019] The light emitting device **1** includes, as its components, a base **10**, three semiconductor laser elements **30**, a submount **40**, a light-reflective member **50**, six protective elements **60**, nine wires **70**, and a lid member **80**.

[0020] The outer shape of the base **10** is rectangular as seen in a top view. The base **10** has a concave shape with a recess inside the outer shape. That is, a recess part that is recessed from an upper surface toward a lower surface is formed in the base **10**. The base **10** includes the upper surface **11**, a bottom surface **12**, the lower surface **13**, inner lateral surfaces **14**, and outer lateral surfaces **17**. The base **10** forms, in the recess, step parts **20** (the step part and the additional step part) each consisting of an upper surface and a lateral surface. The upper surface of each step part **20** is referred to as a step-part upper surface **21**, and the lateral surface of each step part **20** is referred to as a step-part lateral surface **22**.

[0021] The upper surface **11** intersects with the outer lateral surfaces **17** and the inner lateral surfaces **14**, and the lower surface **13** intersects with the outer lateral surfaces **17**. The bottom surface **12** is positioned above the lower surface **13** and lower than the upper surface **11**. In the regions where the step parts **20** are formed, the step-part lateral surfaces **22** intersect with the bottom surface **12**, and the step-part upper surfaces **21** intersect with the inner lateral surfaces **14**. In the region where the step parts **20** are not formed, the bottom surface **12** intersects with the inner lateral surfaces **14**.

[0022] As seen in a top view, the recess part forms space by the recess inside the frame defined by the upper surface **11** of the base **10**. The outer shape of the frame is rectangular as seen in a top view. The step parts **20** are formed inner than (inside of) the frame. The step parts **20** are respectively provided along two inner lateral surfaces **14** which are the opposite two sides of the rectangular outer shape. A long the entire length of the inner lateral surfaces **14** of the two sides, the step parts **20** are respectively provided to intersect with the inner lateral surfaces **14** of the two sides. The inner lateral surfaces **14** of other two sides are not provided with the step parts **20** excluding the intersecting portions.

[0023] Here, the intersecting portion refers to the portion where two surfaces intersect with each other by their ends. The inner lateral surfaces **14** not provided with the step parts **20** excluding the intersecting portions are referred to as the first inner lateral surfaces **15**. The base **10** has a pair of first inner lateral surfaces facing each other. The inner lateral surfaces **14** provided with the step parts **20** are referred to as the second inner lateral surfaces **16** (the second inner lateral surface and the additional second inner lateral surface). The base **10** has a pair of second inner lateral surfaces facing each other. Similarly, the outer lateral surfaces **17** corresponding to the first inner lateral surfaces are referred to as the first outer lateral surfaces **18**. The outer lateral surfaces **17** corresponding to the second inner lateral surfaces are referred to as the second outer lateral surfaces **19**. In distinguishing between two step parts **20** respectively formed along two pieces of the inner lateral surfaces, they are referred to as the first step part and the second step part.

[0024] The second inner lateral surface **16** extends along a plane intersecting with a plane along which the one of the first inner lateral surfaces **15** extends. The additional second inner lateral surface **16** extends along a plane intersecting with a plane along which the one of the first inner lateral surfaces **15** extends. Width of the upper surface **11** from outer lateral surfaces **17** to inner lateral surfaces **14** is identical excluding the intersecting portions. As used herein, the identical width permits a difference of 10%. As seen in a top view, in the distance from the outer lateral surfaces **17** to the bottom surface **12**, the second outer lateral surfaces **19** are greater than the first outer lateral surfaces **18** by the step parts **20**. In this structure, the base **10** is less prone to warp in the manufacturing process in the direction of the second outer lateral surfaces **19** than in the direction of the first outer lateral surfaces **18**.

[0025] In the base **10**, the sides corresponding to the second inner lateral surfaces **16** are longer

than the sides corresponding to the first inner lateral surfaces **15**. The sides corresponding to the second outer lateral surfaces **19** are longer than the sides corresponding to the first outer lateral surfaces **18**. Taking into consideration of the deformation of the base **10** due to warp, the sides corresponding to the first inner lateral surfaces **15** or the first outer lateral surfaces **18** are preferably shorter than the sides corresponding to the second inner lateral surfaces **16** or the second outer lateral surfaces **19** which are less prone to warp. Note that, the sides may be identical to one another in length or the relationship in length between them may be inverted.

[0026] The main material of the base **10** may be ceramic. Ceramic used for the base **10** may be, for example, aluminum nitride, silicon nitride, aluminum oxide, or silicon carbide.

[0027] A plurality of metal films **25** is respectively provided on the lower surface **13** of the base **10** and the step-part upper surfaces **21**. The metal film **25** provided on the lower surface **13** of the base **10** and the metal film **25** provided on the step-part upper surfaces **21** are connected to each other via metal passing inside the base **10** and, therefore, can be electrically connected to each other.

[0028] A plurality of metal films **25** is provided at each of the step-part upper surfaces **21** of the first step part **23** and that of the second step part **24**. The plurality of metal films **25** is symmetrically disposed between the first step part **23** and the second step part **24** so as to oppose to each other. Note that, the metal films **25** are not necessarily disposed to have symmetry between the first step part **23** and the second step part **24**.

[0029] In the step-part upper surface **21** of the step part **20** corresponding to one second inner lateral surface **16**, the plurality of metal films **25** is provided in sequence from one end to other end of the side corresponding to the second inner lateral surface **16**. That is, a line parallel to this side intersects with all the metal films **25** provided on the step-part upper surface **21** corresponding to one second inner lateral surface **16**. Furthermore, a line perpendicular to this side intersects with only one of the metal films **25** provided on the step-part upper surface **21** corresponding to one second inner lateral surface **16**.

[0030] In the base **10**, a bottom part, which includes the bottom surface **12**, and a frame part, which forms the frame surrounding the bottom part and includes the inner lateral surfaces **14** and the step parts **20**, may be formed of different main materials, and the base **10** may be formed having the frame part and the bottom part joined to each other. In this case, for example, the main material of the frame part may be ceramic, and the main material of the bottom part may be metal which is higher in thermal conductivity than the ceramic of the frame part.

[0031] The outer shape of each semiconductor laser element **30** is rectangular as seen in a top view. A lateral surface intersecting with one of two short sides of this rectangle functions as the emitting end surface for light emitted from the semiconductor laser element **30**. The upper surface and the lower surface of the semiconductor laser element **30** are greater in area than the emitting end surface.

[0032] The three semiconductor laser elements **30** are each a multiple-emitter element including two emitters. At the lower surface of the semiconductor laser element **30**, one electrode surface shared by the two emitters is provided. At the upper surface of the semiconductor laser element **30**, two electrode surfaces respectively corresponding to two emitters are provided.

[0033] Laser light emitted from each emitter spreads, and forms an oval far-field pattern (hereinafter referred to as “the FFP”) in a plane parallel to the light emitting end surface. The FFP is the shape of emitted light or light intensity distribution at a position spaced apart from the emitting end surface. Light of which light intensity distribution has an intensity of $1/e^2$ or more to the peak intensity value is referred to as the main portion of the light.

[0034] The three semiconductor laser elements **30** consist of a semiconductor laser element emitting blue-color light, a semiconductor laser element emitting green-color light, and a semiconductor laser element emitting red-color light. As necessary, the three semiconductor laser elements are distinguished from one another by being referred to as a first semiconductor laser element, a second semiconductor laser element, and a third semiconductor laser element.

[0035] For example, in the embodiment shown in FIG. 3, the three semiconductor laser elements **30** consist of a first semiconductor laser element **31** emitting blue-color light, a second semiconductor laser element **32** emitting green-color light, and a third semiconductor laser element **33** emitting red-color light.

[0036] As used herein, the blue-color light refers to light of which peak emission wavelength falls within a range of 420 nm to 494 nm inclusive. The green-color light refers to light of which peak emission wavelength falls within a range of 495 nm to 570nm inclusive. The red-color light refers to light of which peak emission wavelength falls within a range of 605 nm to 750 nm inclusive.

[0037] As seen in a top view, the outer shape of the first semiconductor laser element **31** and the outer shape of the second semiconductor laser element **32** are identical to each other in the length of the long side of the rectangular shape. As used herein, the identical length permits a difference of 20%. As seen in a top view, the outer shape of the third semiconductor laser element **33** is greater in the length of the long side of the rectangle shape than that of the first semiconductor laser element **31** and that of the second semiconductor laser element **32**. Specifically, the long side of the third semiconductor laser element **33** is longer by 20% or more than the longer one of the long side of the first semiconductor laser element **31** and the long side of the second semiconductor laser element **32**.

[0038] Note that, the semiconductor laser elements **30** may each be a single-emitter element including only one emitter. The semiconductor laser elements **30** may include both of a single-emitter element and a multiple-emitter element. The number of the plurality of semiconductor laser elements is not limited to three. The light emitted by the semiconductor laser elements **30** is not specified to those described above. The semiconductor laser elements **30** emitting light of an identical color may be disposed.

[0039] The terms “first” to “third” distinguishing the three semiconductor laser elements **30** may refer to different target semiconductor laser elements than those used above. For example, the semiconductor laser element emitting red-color light may be referred to as the first semiconductor laser element; the semiconductor laser element emitting blue-color light may be referred to as the second semiconductor laser element; and the semiconductor laser element emitting green-color light may be referred to as the third semiconductor laser element.

[0040] For example, the semiconductor laser element having a rectangular outer shape as seen in a top view of which long side is great may be referred to as the first semiconductor laser element, and the semiconductor laser element of which short side is small may be referred to as the second semiconductor laser element. The terms “first”, “second” and the like are merely signs used for distinction, and may be used as appropriate according to the intent of distinction.

[0041] The submount **40** is rectangular prism-shaped. In the submount **40**, the sides in the height direction are the smallest. The submount **40** is formed of, for example, silicon nitride, aluminum nitride, or silicon carbide. Without being specified thereto, other materials may be used. The metal film **25** is provided at the upper surface of the submount **40**.

[0042] The light-reflective member **50** includes a lower surface and a light-reflective surface which is inclined relative to the lower surface. The light-reflective surface is flat, and designed to form an angle of 45 degrees relative to the lower surface of the light-reflective member **50**. This angle is not specified to 45 degrees. The light-reflective surface may be a curved surface.

[0043] The main material of the light-reflective member **50** may be glass, metal or the like. The main material is preferably heat resistant, and may be, for example, quartz or glass such as BK 7 (borosilicate glass), metal such as Al, or Si. As the light-reflective surface, a dielectric multilayer film of metal such as Ag, Al or the like or Ta.sub.2O.sub.5/SiO.sub.2, TiO.sub.2/SiO.sub.2, Nb.sub.2O.sub.5/SiO.sub.2 or the like may be employed.

[0044] The light-reflective surface may have a light reflectivity of 99% or more to the peak wavelength of laser light irradiated to the light-reflective surface. The light reflectivity may be 100% or less or less than 100%. The protective elements **60** are provided to avoid overcurrent for

specific elements (for example, the semiconductor laser elements **30**). The protective elements **60** may be, for example, Zener diodes. The Zener diodes may be formed of Si. The wires **70** are, for example, metal wires. The lid member **80** is formed to have a rectangular prism shape. In the lid member **80**, sides in height direction are the shortest. The main material of the lid member **80** is a light-transmissive material. The main material may be, for example, sapphire. Sapphire is relatively high in refractive index and also in strength. At the peripheral region of the lower surface of the lid member **80**, a metal film for bonding is provided.

[0045] The lid member **80** may have an opaque region at part of the upper surface or the lower surface. For example, a region highly reflective or light-shielding may be partially provided. The shape is not specified to a rectangular prism. The main material of the lid member **80** may be glass or the like.

[0046] Next, a description will be given of the light emitting device **11** made up of the above-described elements.

[0047] Firstly, the protective elements **60** are disposed on the step-part upper surfaces **21**. For example, when the protective elements are formed of Si, the base **10** is preferably formed of ceramic than resin in view of bondability, because the difference in coefficient of linear expansion between the ceramic base **10** and the protective elements is smaller.

[0048] One protective element **60** corresponds to one emitter of the semiconductor laser element **30**. That is, for one semiconductor laser element **30** including two emitters, two protective elements **60** are provided. In this manner, inner the frame of the light emitting device **1**, the protective elements **60** are provided in a number greater than the semiconductor laser elements **30**. Provision of at least one protective element on the step-part upper surface **21** contributes to downsizing the light emitting device **1**.

[0049] Each of two protective elements **60** corresponding to one semiconductor laser element **30** are connected to two metal films **25** provided at the step-part upper surface **21**, so that one of the two metal films **25** is electrically connected to the cathode electrode and the other of the two metal films **25** is electrically connected to the anode electrode.

[0050] Each protective element **60** is disposed across the metal film **25** of the cathode electrode and the metal film **25** of the anode electrode. In this manner, the protective element **60** is electrically connected without using a wire. Accordingly, the protective element **60** is electrically connected to two metal films **25** placed next to each other on the step-part upper surface **21**.

[0051] Instead of disposing each protective element **60** across two metal films **25**, electrical connection may be established using wires **71**. FIG. 7 shows a modified example of a light emitting device **1A** in which a protective element **60** is disposed on one of two metal films **25** and a wire **71** connects between the protective element **60** and the other of the two metal film **25**. In this case, the protective element **60** is previously disposed, and then the wire **71** is connected to the protective element **60** and the metal film **25**. Note that, when this wire is to be distinguished from the wire **70** which is used for electrically connecting the semiconductor laser element **30**, the wire **70** and the wire **71** are respectively referred to as a first wire and a second wire.

[0052] The protective elements **60** are disposed on the step-part upper surfaces **21** of the step parts **20** provided over the entire length of the sides corresponding to the second inner lateral surfaces **16** of the recess, in the vicinity of ends of the sides as seen in a top view. Here, in each of the first step part **23** and the second step part **24**, two protective elements **60** are disposed in the vicinity of one end of the side, and one protective element **60** is disposed in the vicinity of the other end of the side. Each of the upper surface of the step part **20** and an upper surface of the additional step part **20** has at least one of the protective elements **60** arranged thereon. While the details will be given later, this disposition facilitates wire bonding of the semiconductor laser elements **30** in conjunction with the disposition relationship of the semiconductor laser elements **30** and the light-reflective member **50**.

[0053] Next, three semiconductor laser elements **30** are disposed on the submount **40** so as to be

juxtaposed to (aligned along) one another. The electrode surface at the lower surface of each of the three semiconductor laser elements **30** is bonded to the metal film provided on the upper surface of the submount **40**. Beside the first semiconductor laser element **31**, the second semiconductor laser element **32** is disposed. Beside the second semiconductor laser element **32**, the third semiconductor laser element **33** is disposed.

[0054] That is, the first semiconductor laser element **31** and the second semiconductor laser element **32** are adjacent to each other, and the second semiconductor laser element **32** and the third semiconductor laser element **33** are adjacent to each other. The second semiconductor laser element **32** is interposed between the first semiconductor laser element **31** and the third semiconductor laser element **33**. Note that, the third semiconductor laser element **33** may be disposed so as to be adjacent to the first semiconductor laser element **31** instead of the second semiconductor laser element **32**.

[0055] The three semiconductor laser elements **30** are arranged such that their emitting end surfaces face one lateral surface of the submount **40**. The emitting end surfaces are disposed at a plane identical to the lateral surface of the submount **40**, or disposed outward than the lateral surface of the submount **40**. This lateral surface of the submount **40** is referred to as the emitting-end-surface-side lateral surface. This disposition prevents the emitted light from being directly irradiated to the upper surface of the submount **40**.

[0056] The submount **40** can also perform to dissipate heat generated by the semiconductor laser elements **30**. Specifically, the submount **40** should be formed with a material being higher in thermal conductivity than the semiconductor laser elements **30**. Accordingly, when the submount **40** exhibits this performance, the submount **40** can be regarded as a heat dissipating member. By the semiconductor laser elements being bonded to the submount **40** by their lower surfaces which are greater in area than their emitting end surfaces, heat dissipating property improves.

[0057] The light emitting position of the semiconductor laser elements **30** is increased by the submount **40** on which the semiconductor laser elements **30** are disposed. That is, the submount **40** raises the light emitting position higher, thereby performing to adjust the position of light emitted onto the light-reflective surface. Accordingly, the submount **40** can be regarded as the adjusting member. Note that, the submount **40** may be individually provided for each of the semiconductor laser elements **30**. Next, the submount **40** on which the semiconductor laser elements **30** are disposed is disposed on the bottom surface **12** of the base **10**. The submount **40** is disposed on the bottom surface **12** inside the frame formed by the frame part of the base **10**. The submount **40** is disposed on the bottom surface **12** inside the step parts **20** of the base **10**.

[0058] The submount **40** is disposed such that the emitting end surface of the semiconductor laser element **30** opposes to the first inner lateral surface **15** of the base **10**. The submount **40** is disposed such that the lateral surface of the semiconductor laser element **30** opposite to the emitting end surface opposes to the first inner lateral surface **15** opposite to the first inner lateral surface **15** to which the emitting end surfaces oppose. The submount **40** is disposed such that two lateral surfaces intersecting with the emitting end surface of each semiconductor laser element **30** opposes to the second inner lateral surface **16** of the base **10** or the lateral surface of the adjacent semiconductor laser element **30** intersecting with the emitting end surface.

[0059] Accordingly, the emitted light from the semiconductor laser elements **30** travels toward the first inner lateral surface **15**. In particular, from every semiconductor laser element, if light emitted to the direction perpendicular to the emitting end surface (hereinafter referred to as light of the optical axis) traveled straight, the light of the optical axis would become incident on the first inner lateral surface **15**. The emitting end surfaces and the first inner lateral surface **15** on which the light of the optical axis would become incident are parallel to each other. The second inner lateral surfaces **16** include a region which is parallel to the lateral surfaces which intersect with the emitting end surfaces. As used herein, being parallel permits a difference of ± 5 degrees. This region may not necessarily be parallel. The first semiconductor laser element **31** is arranged closer to the

first step part **23** than the second semiconductor laser element **32**. The second semiconductor laser element **32** is arranged closer to the second step part **24** than the first semiconductor laser element **31**. The third semiconductor laser element **33** is arranged closer to the second step part **24** than the second semiconductor laser element **32**.

[0060] Next, the light-reflective member **50** is disposed on the bottom surface **12** of the base **10**. The light-reflective member **50** reflects light emitted from all the three semiconductor laser elements **30** disposed on the bottom surface **12**. Accordingly, the light-reflective member **50** is disposed such that the light-reflective surface of the light-reflective member **50** is oriented toward the emitting end surfaces. As seen in a top view, the sides corresponding to the upper edge and the lower edge of the inclination of the light-reflective surface and the emitting-end-surface-side lateral surface of the submount **40** become parallel to each other. The light of the optical axis is reflected at the light-reflective surface, whereby the light travels upward perpendicularly to the bottom surface **12**. As used herein, being perpendicular permits a difference of ± 5 degrees.

[0061] Note that, in place of a single light-reflective member **50** reflecting light from all the semiconductor laser elements **30**, the light-reflective members **50** may be individually disposed for each of the semiconductor laser elements **30**, to reflect light from corresponding semiconductor laser element.

[0062] In the state where the light-reflective member **50** and the submount **40** are disposed so as to reflect the emitted light from the semiconductor laser elements **30**, in the smallest rectangular covering the light-reflective member **50** and the submount **40** as seen in a top view, a width perpendicular to the light emitting end surface is longer than a width parallel to the light emitting end surface. Accordingly, the submount **40** and the light-reflective member **50** are disposed in a compact manner for the light emitting device **1** of which side of the base **10** corresponding to the second inner lateral surface **16** is longer than side of the base **10** corresponding to the first inner lateral surface **15**.

[0063] Here, a description will be given of the disposition relationship among the semiconductor laser elements **30**, the submount **40**, the light-reflective member **50**, and the protective elements **60**. In comparing the disposition relationship, being in the direction toward which light travels from the semiconductor laser elements **30** is referred to as being on the light traveling side, and being in the opposite direction is referred to as being on the element side. For example, when opposing first inner lateral surfaces **15** are compared with each other, the first inner lateral surface **15** in the direction of traveling light emitted from the semiconductor laser elements is regarded as the light traveling side of the first inner lateral surface **15**, and the first inner lateral surface **15** on the opposite side is regarded as the element-side of the first inner lateral surface **15**.

[0064] The three protective elements **60** disposed on the step-part upper surface **21** of the step part **20** provided along one second inner lateral surface **16** are distinguished from one another by being referred to as the first protective element **61**, the second protective element **62**, and the third protective element **63** in sequence from the light traveling side to the element side.

[0065] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16**, so that the emitting end surfaces of the semiconductor laser elements **30** are positioned closer to one of the first inner lateral surfaces **15** on the light traveling side than a center position between the first inner lateral surfaces **15**. That is, the distance from the emitting end surfaces of the semiconductor laser elements **30** to the light traveling side of the first inner lateral surface **15** is smaller than the distance from the center of opposing first inner lateral surfaces **15** to the light traveling side of the first inner lateral surface **15**. Accordingly, the light emitting end surface of the semiconductor laser element **30** is disposed on the light traveling side than a center in the space in the recess.

[0066] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16**, so that the lateral surfaces of the semiconductor laser elements **30** opposite to the emitting end surfaces are positioned closer to the other of the first inner lateral surfaces **15** on the

element side than the center position between the first inner lateral surfaces **15**. This disposition relationship is similarly applied to all of the first semiconductor laser element **31**, the second semiconductor laser element **32**, and the third semiconductor laser element **33**.

[0067] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16**, so that the emitting-end-surface-side lateral surface of the submount **40** is positioned closer to one of the first inner lateral surfaces **15** on the light traveling side than the center position between the first inner lateral surfaces **15**. With respect to the direction parallel to the second inner lateral surfaces **16**, the lateral surface of the submount **40** opposite to the emitting-end-surface-side lateral surface is positioned closer to the other of the first inner lateral surfaces **15** on the element side than the center position between the first inner lateral surfaces **15**. Accordingly, the submount **40** is provided from the light traveling side to the element side with the center in the space in the recess as the boundary.

[0068] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16**, so that the barycenter of the submount **40** is positioned closer to the other of the first inner lateral surfaces **15** on the element side than the center position between the first inner lateral surfaces **15**. Accordingly, as a whole, the submount **40** is provided shifted to the element side from the center in the space in the recess.

[0069] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16** or the second outer lateral surface **19**, so that the emitting end surfaces of the semiconductor laser elements **30** are positioned closer to one of the first outer lateral surfaces **18** on the light traveling side than a center position between the first outer lateral surfaces **18**.

Accordingly, the light emitting end surfaces of the semiconductor laser element **30** are provided shifted to the light traveling side from a center of the base **10** based on the outer shape of the base **10** or a center of the light emitting device **1** based on the outer shape of the light emitting device **1**.

[0070] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16** or the second outer lateral surface **19**, so that the lateral surface of the semiconductor laser element **30** on the side opposite to the emitting end surface is positioned closer to the other of the first outer lateral surface **18** on the element side than the center position between the first outer lateral surfaces **18**.

[0071] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16** or the second outer lateral surface **19**, so that the emitting-end-surface-side lateral surface of the submount **40** is positioned closer to one of the first outer lateral surfaces **18** on the light traveling side than the center position between the first outer lateral surfaces **18**. The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16** or the second outer lateral surface **19**, so that the lateral surface of the submount **40** on the side opposite to the emitting-end-surface-side lateral surface is positioned closer to the other of the first outer lateral surfaces **18** on the element side than the center position between the first outer lateral surfaces **18**. Accordingly, the submount **40** is provided from the light traveling side to the element side with the center based on the outer shape of the base **10** or the outer shape of the light emitting device **1** as the boundary.

[0072] The submount **40** is disposed, with respect to the direction parallel to the second inner lateral surface **16** or the second outer lateral surface **19**, so that the barycenter of the submount **40** is positioned closer to the other of the first outer lateral surfaces **18** on the element side than the center position between the first outer lateral surfaces **18**. Accordingly, as a whole, the submount **40** is provided shifted to the element side from the center according to the outer shape of the base **10** or the outer shape of the light emitting device **1**.

[0073] The light-reflective member **50** is disposed so as to be included in the region on the light traveling side than a plane passing through the center of the opposing first inner lateral surfaces **15** and parallel to the first inner lateral surfaces **15**. The light-reflective member **50** is disposed so as to be included in the region on the light traveling side than a plane passing through the center of the

opposing first outer lateral surfaces **18** and parallel to the first inner lateral surfaces **15** or the first outer lateral surfaces **18**. With reference to the direction parallel to the second inner lateral surfaces **16**, the light-reflective member **50** is shorter than the submount **40**.

[0074] In relation to the semiconductor laser element **30**, the first protective element **61** is disposed on the light traveling side than a plane including the emitting end surface of any one of the three semiconductor laser elements **30**. The first protective element **61** is disposed on the upper surface of the step part **20** and on the light traveling side of the laser light from any one of the three semiconductor laser elements **30** with respect to a plane including an emitting end surface of the one of the three semiconductor laser elements **30**. In relation to the submount **40**, the first protective element **61** is disposed on the light traveling side than a plane including the emitting-end-surface-side lateral surface of the submount **40**. In relation to the light-reflective member **50**, as seen in a top view, the first protective element **61** is disposed on the light traveling side than a line including the side being the lower edge of the light-reflective surface. As seen in a top view, the first protective element **61** intersects with a line including the side being the upper edge of the light-reflective surface. Note that, the first protective element **61** may be disposed on the element side than this line.

[0075] In relation to the semiconductor laser element **30**, the second protective element **62** is disposed on the light traveling side than the plane including the emitting end surface of any one of the three semiconductor laser elements **30**. The second protective element **62** is disposed on the upper surface of the step part **20** and on the light traveling side of the laser light from any one of the three semiconductor laser elements **30** with respect to a plane including an emitting end surface of the one of the three semiconductor laser elements **30**. In relation to the submount **40**, the second protective element **62** is disposed on the light traveling side than the plane including the emitting-end-surface-side lateral surface of the submount **40**. In relation to the light-reflective member **50**, as seen in a top view, the second protective element **62** intersects with the line including the side being the lower edge of the light-reflective surface. As seen in a top view, the second protective element **62** is disposed on the element side than the line including the upper edge of the light-reflective surface. Note that, the second protective element **62** may be disposed so as to intersect with the plane including the emitting end surface of at least one of the semiconductor laser elements **30**.

[0076] In relation to the semiconductor laser elements **30**, the third protective element **63** is disposed on the element side than the plane including the emitting end surface of any one of the three semiconductor laser elements **30**. In relation to the submount **40**, the third protective element **63** is disposed on the element side than the plane including the emitting-end-surface-side lateral surface of the submount **40**. The third protective element **63** is disposed on the light traveling side than a plane including the lateral surface opposite to the emitting-end-surface-side lateral surface. In relation to the light-reflective member **50**, as seen in a top view, the third protective element **63** is disposed on the element side than the line including the side being the lower edge of the light-reflective surface. Note that, the third protective element **63** may be disposed so as to intersect with the plane including the lateral surface opposite to the emitting-end-surface-side lateral surface.

[0077] The thickness of the submount **40** from the lower surface to the upper surface is greater than the height from the bottom surface **12** to the side being the lower edge of the light-reflective surface. The height from the bottom surface **12** to the step-part upper surface **21** is greater than the height from the bottom surface **12** to the upper surface of the semiconductor laser element **30**. Accordingly, the light emitting position in the emitting end surface of the semiconductor laser element **30** is higher than the lower edge of the light-reflective surface; higher than the upper surface of the submount **40**; and lower than the step-part upper surfaces **21**. The height from the bottom surface **12** to the top of the light-reflective member **50** is greater than the height from the bottom surface **12** to the step-part upper surfaces **21**.

[0078] Next, in order to electrically connect the semiconductor laser elements **30**, a plurality of wires **70** is bonded. Each wire **70** has one end bonded to the upper surface of corresponding

semiconductor laser element **30** or the upper surface of the submount **40**, and has the other end bonded to corresponding step-part upper surface **21**. In the present embodiment, the electrode surfaces respectively corresponding to two emitters are provided at the upper surface. Therefore, one ends of corresponding two wires **70** are respectively bonded to the electrode surfaces of different emitters. One end of one wire **70** is bonded to the submount **40** electrically connected to the electrode surface of the lower surface of the semiconductor laser element **30**.

[0079] In the present embodiment, three semiconductor laser elements **30** each including two emitters are provided, and the electric circuit is designed so as to control ON/OFF of light emission by one emitter. Accordingly, the semiconductor laser elements **30** are connected to wires so that power supply and voltage supply can be controlled for each emitter. In the light emitting device **1**, nine wires **70** in total are bonded to any of the plurality of metal films **25**. The nine wires are respectively bonded to different ones of the metal films **25**, and establish electrical connection.

[0080] To one semiconductor laser element **30**, three wires **70** are connected. One semiconductor laser element **30** is connected to one cathode electrode, and two emitters of one semiconductor laser element **30** are connected to different anode electrodes, respectively. One emitter and one protective element **60** are electrically connected in parallel. That is, the cathode electrode is provided for each semiconductor laser element **30**, and the anode electrode is provided for each emitter of each semiconductor laser element **30**. To one anode electrode, one protective element **60** is connected.

[0081] Note that, control may be exerted for each semiconductor laser element, that is, ON/OFF may be controlled by multiple emitters. In accordance with the control manner or the number of semiconductor laser elements, the number of the protective element or the wires is determined as appropriate. For example, when control is exerted for each semiconductor laser element, one protective element **60** and two wires **70** may correspond to one semiconductor laser element **30**.

[0082] The three wires **70** electrically connected to the first semiconductor laser element **31** are bonded to the metal films **25** provided onto the step-part upper surface **21** of the first step part **23**. The three wires **70** electrically connected to the second semiconductor laser element **32** are bonded to the metal films **25** provided onto the step-part upper surface **21** of the second step part **24**. Accordingly, the three wires **70** electrically connected to the first semiconductor laser element **31** are bonded to the metal films **25** of one second inner lateral surface **16** side, and the three wires **70** electrically connected to the second semiconductor laser element **32** are bonded to the metal films **25** of the other second inner lateral surface **16** side.

[0083] All the wires **70** electrically connected to the first semiconductor laser element **31** are not bonded to the step-part upper surface **21** of the step part **20** (the second step part **24**) formed along the second inner lateral surface **16** to which the second semiconductor laser element **32** is closer than the first semiconductor laser element **31** is. Similarly, all the wires **70** electrically connected to the second semiconductor laser element **32** are not bonded to the step-part upper surface **21** of the step part **20** (the first step part **23**) formed along the second inner lateral surface **16** to which the first semiconductor laser element **31** is closer than the second semiconductor laser element **32** is. This configuration reduces the risk of the wires crossing each other and brought into contact with each other.

[0084] Out of the three wires **70** electrically connected to the third semiconductor laser element **33**, one is bonded to the metal film **25** of one second inner lateral surface **16** side, and two are bonded to the metal films **25** of the other second inner lateral surface **16** side. That is, the wires **70** are arranged in a dispersed manner to the first step part **23** and the second step part **24**.

[0085] All the wires **70** electrically connected to the third semiconductor laser element **33** are bonded to the third semiconductor laser element **33** in region projecting toward the element side than the first semiconductor laser element **31** and the second semiconductor laser element **32**. That is, the third semiconductor laser element **33** is greater in the length of the long side than the first semiconductor laser element **31** and the second semiconductor laser element **32**, and projects on the

side opposite to the emitting end surface. In this projecting portion, the wires **70** have their one ends bonded to the upper surface electrode of the third semiconductor laser element **33**.

[0086] A plurality of wires **70** of which one ends bonded to the semiconductor laser elements **30** or the submount **40** are bonded to the metal films **25** on the step parts **20** at the other ends. In relation to the semiconductor laser elements **30**, the wires **70** are bonded on the element side than the plane including the emitting end surface of any one of the three semiconductor laser elements **30**. In relation to the submount **40**, the wires **70** are bonded on the element side than the plane including the emitting-end-surface-side lateral surface of the submount **40**.

[0087] In relation to the light-reflective member **50**, the plurality of wires **70** bonded to the semiconductor laser elements **30** or the submount **40** is not bonded on the light traveling side than the line including the side being the lower edge of the light-reflective surface as seen in a top view. These wires **70** are not bonded on the light traveling side than the line including the side being the upper edge of the light-reflective surface as seen in a top view. These wires **70** are arranged so as not to overlap with the light-reflective surface of the light-reflective member **50** as seen in a top view.

[0088] One ends of the wires **70** are bonded to the upper surface of the submount **40** or the upper surfaces of the semiconductor laser elements **30**, and the other ends of the wires **70** are bonded to the step-part upper surfaces **21** at a position higher than the upper surface of the submount **40** and the upper surfaces of the semiconductor laser elements **30**. Accordingly, if the wires **70** overlapped with the light-reflective surface as seen in a top view, portion of light reflected at the light-reflective surface might be incident on the wires **70**. Accordingly, the wires **70** are desirably not on the optical path. To this end, as an example, the wires **70** may be bonded on the element side than a plane including the light emitting end surfaces. In the light emitting device **1**, the wires **70** are bonded in such a manner. Note that, the step-part upper surfaces **21** may be at a lower position.

[0089] In order to bond the wires **70** in this manner, in the light emitting device **1**, the protective elements **60** are disposed closer to the ends of the step-part upper surfaces **21** than the central region thereof. Specifically, the first protective element **61** and the second protective element **62** are provided shifted to the light traveling side, and the third protective element **63** is provided shifted to the element side. Disposing at least one protective element **60** in the region where bonding of the wires **70** is not desirable, efficient wiring pattern is realized.

[0090] One of the wires **70** electrically connected to the first semiconductor laser element **31** is bonded to the metal film **25** on which the protective element **60** is disposed. One of the wires **70** electrically connected to the second semiconductor laser element **32** is bonded to the metal film **25** where the protective element **60** is disposed. Specifically, these wires are bonded to the metal films **25** where the second protective elements **62** are disposed.

[0091] The three wires **70** electrically connected to the third semiconductor laser element **33** are bonded to the metal film **25** where the protective elements **60** are disposed. Two wires **70** corresponding to two emitters are bonded to the metal films **25** where the protective elements **60** are disposed. Specifically, the wires are bonded to the metal films **25** where the third protective elements **63** are disposed. That is, the plurality of metal films **25** includes the metal films **25** to which the protective elements **60** and the wires **70** are bonded.

[0092] The first protective element **61** and the second protective element **62**, which are disposed on the step-part upper surface **21** of the step part **20** (the first step part **23**) formed along the second inner lateral surface **16** on the side where the wires **70** electrically connected to the first semiconductor laser element **31** are bonded, protect the first semiconductor laser element **31**. The first protective element **61** and the second protective element **62**, which are disposed on the step-part upper surface **21** of the step part **20** (the second step part **24**) formed along the second inner lateral surface **16** on the side where the wires **70** electrically connected to the second semiconductor laser element **32** are bonded, protect the second semiconductor laser element **32**. Two third protective elements **63** disposed on the step-part upper surfaces **21** of the step parts **20**

(the first step parts **23** and the second step part **24**) formed along two second inner lateral surfaces **16** protect the third semiconductor laser element **33**.

[0093] Between the first protective element **61** and the second protective element **62** disposed on the step-part upper surface **21** of one step part **20** (one of the first step part **23** and the second step part **24**), no region for bonding the wire **70** bonded to the semiconductor laser element **30** is provided. Similarly, between these protective elements, no region for bonding the wire **70** bonded to the submount **40** is provided.

[0094] In the light emitting device **1** configured in this manner, a line being parallel to the first inner lateral surface **15** and intersecting with the light-reflective member **50** and the first protective elements **61** as seen in a top view can be drawn virtually. In other words, in the light emitting device **1**, the light-reflective member **50** and at least one of first protective elements **61** are disposed so as to intersect with a line parallel to the first inner lateral surface **15**. Disposing the first protective elements **61** at regions not desirable for bonding the wires **70** realizes a wiring pattern which makes effective use of the step-part upper surfaces **21** and contributes to reducing the size.

[0095] Accordingly, in the light emitting device **1**, one of the protective elements **60** disposed on the most light traveling side and the light-reflective member **50** are disposed so as to intersect with the line parallel to the first inner lateral surface **15**. Alternatively, one of the protective elements **60** on the most light traveling side intersect with a line being parallel to the first inner lateral surfaces **15** and crossing at least any part in the light-reflective member **50**. This configuration is common to each step parts **20** formed at the two second inner lateral surfaces **16**.

[0096] In the light emitting device **1**, as seen in a top view, a line being parallel to the first inner lateral surface **15** and intersecting with the light-reflective member **50** and the second protective elements **62** can be drawn virtually. In other words, in the light emitting device **1**, the light-reflective member **50** and at least one of second protective elements **62** are disposed so as to intersect with a straight line which is a line parallel to the first inner lateral surface **15**.

[0097] Accordingly, in the light emitting device **1**, each of all the protective elements **60** disposed on the light traveling side than the center of the opposing first inner lateral surfaces **15** and the light-reflective member **50** are disposed so as to intersect with a line parallel to the first inner lateral surfaces **15**. Alternatively, each of all the protective elements **60** disposed on the light traveling side than the center of the opposing first inner lateral surfaces **15** intersect with a line being parallel to the first inner lateral surfaces **15** and crossing at least any part in the light-reflective member **50**. This configuration is common to each step parts **20** formed at the two second inner lateral surfaces **16**.

[0098] In this manner, with reference to the disposition relationship of the light-reflective member **50**, in the step parts **20** formed along the two second inner lateral surfaces **16**, the regions not desirable for bonding the wires **70** have symmetry. A plurality of metal films provided on each of the step-part upper surfaces **21** are arranged symmetrically. Accordingly, the wiring pattern is realized making efficient use of the regions.

[0099] Next, the lid member **80** is bonded to the upper surface of the base **10**. The metal films respectively provided at the bonding region of the lid member **80** and that of the base **10** are bonded to each other through Au-Sn or the like thereby fixed. Here, the base **10** and the lid member **80** are bonded to each other so that the space where the semiconductor laser elements **30** are disposed becomes hermetically sealed space. Such hermetic sealing avoids organic substances or the like from gathering at the light emitting end surfaces of the semiconductor laser elements **30**.

[0100] The lid member **80** is also a light-transmissive member for transmitting light reflected at the light-reflective surface of the light-reflective member **50**. Here, being light transmissive refers to exhibiting transmittance of 80% or more to light emitted from the semiconductor laser elements **30** and becoming incident on the light-transmissive member.

[0101] Thus, the light emitting device according to the present embodiment is designed to have a compact outer shape, while a plurality of semiconductor laser elements and a plurality of protective

elements are disposed in the cavity of the base. In the base, the wiring pattern is realized for such a compact design. Furthermore, by virtue of the elements being disposed taking into consideration of the optical path, the function as the light emitting device is sufficient.

[0102] In the foregoing, a description has been given of the light emitting device according to the embodiment. The light emitting device of the present disclosure is not strictly specified to the light emitting device according to the embodiment. That is, the present disclosure can be implemented without being specified to the outer shape or the structure of the light emitting device disclosed by the embodiment. Furthermore, in applying the present disclosure, not all the constituents are essential. For example, when part of the constituents of the light emitting device disclosed in the embodiment is not recited in the scope of claims, a person skilled in the art can replace, omit, deform, or change the material of the part of the constituents. Thus, flexibility in design as to such part is permitted, in conjunction with the inventive aspects recited in the scope of claims.

[0103] The light emitting device according to the embodiment is applicable to a head-mounted display, a projector, a vehicle headlight, illumination, a display and the like.

Claims

1. A light emitting device comprising: a plurality of semiconductor laser elements; a frame part surrounding a bottom surface on which the semiconductor laser elements are disposed, the frame part having a pair of first inner lateral surfaces facing each other and a second inner lateral surface intersecting at least one of the first inner lateral surfaces; one or more light-reflective members disposed on the bottom surface inside of the frame part, and configured to reflect laser light traveling from the semiconductor laser elements toward one of the first inner lateral surfaces of the frame part; a plurality of wires electrically connecting the semiconductor laser elements; and one or more protective elements including a first protective element, wherein the wires are not bonded to an upper surface of the frame part on a light traveling side beyond a virtual line coinciding with a side defining an upper edge of a light-reflective surface of the light-reflective member, the wires include a first wire and a second wire that are bonded to the upper surface of the frame part in a first region extending along the second inner lateral surface, the first protective element is arranged in the first region, and the first wire is bonded to the upper surface of the frame part in the first region at a position on the light traveling side of the first protective element, and the second wire is bonded to the upper surface of the frame part in the first region at a position on an element-side of the first protective element.

2. The light emitting device according to claim 1, wherein the wires further includes one or more wires different from the first wire bonded to the upper surface of the frame part in the first region at positions on the light traveling side of the first protective element, and a number of the one or more wires bonded to the upper surface of the frame part in the first region at the positions on the light traveling side of the first protective element is larger than a number of the wires bonded to the upper surface of the frame part in the first region at positions on the element-side of the first protective element.

3. The light emitting device according to claim 2, wherein the second wire is connected to one of the semiconductor laser elements that is different from the semiconductor laser elements bonded with the one or more wires bonded to the upper surface of the frame part in the first region at the positions on the light traveling side of the first protective element.

4. The light emitting device according to claim 1, wherein the one or more protective elements are not arranged at a position in the first region on the element-side of the position at which the second wire is bonded to the upper surface of the frame part.

5. The light emitting device according to claim 1, wherein the one or more protective elements further includes a second protective element arranged on the upper surface of the frame part in a second region extending along an inner lateral surface facing the second inner lateral surface, the

wires further include a third wire bonded to the upper surface of the frame part in the second region at a position on the light traveling side of the second protective element, and a fourth wire bonded to the upper surface of the frame part in the second region at a position on the element-side of the second protective element, and the first wire is bonded to one of the semiconductor laser elements at a position on the element side of the third wire.

6. The light emitting device according to claim 5, wherein the frame part further includes a step part formed along the second inner lateral surface and along the inner lateral surface facing the second inner lateral surface, and the first region and the second region are located on an upper surface of the step part.

7. The light emitting device according to claim 1, further comprising a plurality of metal films provided in the first region, and the first protective element is arranged over two adjacent ones of the metal films.

8. The light emitting device according to claim 7, wherein the first wire is bonded to one of the two adjacent ones of the metal films, and the second wire is bonded to the other of the two adjacent ones of the metal films.

9. The light emitting device according to claim 1, wherein a number of the wires bonded to the upper surface of the frame part in the first region on the element-side of the emitting end surfaces of the semiconductor laser elements is larger than a number of the one or more protective elements arranged in the first region on the element-side of the emitting end surfaces of the semiconductor laser elements.

10. The light emitting device according to claim 1, further comprising one or more submounts on which the semiconductor laser elements are mounted, and the wires are bonded to the semiconductor laser elements or the one or more submounts.

11. The light emitting device according to claim 10, wherein the semiconductor laser elements include a first semiconductor laser element and a second semiconductor laser element, the first semiconductor laser element is arranged closer to the second inner lateral surface than the second semiconductor laser element, the first wire is bonded to the first semiconductor laser element or one of the one or more submounts on which the first semiconductor laser element is mounted, and the second wire is bonded to the second semiconductor laser element or one of the one or more submounts on which the second semiconductor laser element is mounted.

12. The light emitting device according to claim 11, wherein the semiconductor laser elements further include a third semiconductor laser element arranged between the first semiconductor laser element and the second semiconductor laser element.

13. The light emitting device according to claim 10, wherein the semiconductor laser elements include a first semiconductor laser element and a second semiconductor laser element, the first semiconductor laser element is arranged closer to the second inner lateral surface than the second semiconductor laser element, the first wire is bonded to the second semiconductor laser element or one of the one or more submounts on which the second semiconductor laser element is mounted, and the second wire is bonded to the first semiconductor laser element or one of the one or more submounts on which the first semiconductor laser element is mounted.

14. The light emitting device according to claim 13, wherein the semiconductor laser elements further include a third semiconductor laser element, and the second semiconductor laser element is arranged closer to the second inner lateral surface than the first semiconductor laser element.

15. The light emitting device according to claim 1, wherein the second wire is bonded to the upper surface of the frame part in the first region at a position on the element-side of the semiconductor laser elements, at least a part of the first protective element is arranged on the element-side of the semiconductor laser elements in the first region, and the first wire is bonded to the upper surface of the frame part in the first region at a position between a plane that coincides with edges on the light traveling side of the semiconductor laser elements and that is parallel to the first inner lateral surface and a plane that coincides with edges on the element-side of the semiconductor laser

elements and that is parallel to the first inner lateral surface.

16. The light emitting device according to claim 1, wherein the second wire is bonded to the upper surface of the frame part in the first region at a position on the element-side of the semiconductor laser elements, at least a part of the first protective element is arranged in the first region at a position between a plane that coincides with edges on the light traveling side of the semiconductor laser elements and that is parallel to the first inner lateral surface and a plane that coincides with edges on the element-side of the semiconductor laser elements and that is parallel to the first inner lateral surface, and the first wire is bonded to the upper surface of the frame part in the first region at a position between the plane that coincides with the edges on the light traveling side of the semiconductor laser elements and that is parallel to the first inner lateral surface and the plane that coincides with the edges on the element-side of the semiconductor laser elements and that is parallel to the first inner lateral surface.

17. The light emitting device according to claim 11, wherein the second wire is bonded to the upper surface of the frame part in the first region at a position on the element-side of the one or more submounts, at least a part of the first protective element is arranged in the first region at a position between a plane that coincides with edges on the element-side of the semiconductor laser elements and that is parallel to the first inner lateral surface and a plane that coincides with edges on the element-side of the one or more submounts and that is parallel to the first inner lateral surface, and the first wire is bonded to the upper surface of the frame part in the first region at a position between a plane that coincides with edges on the light traveling side of the one or more submounts and that is parallel to the first inner lateral surface and the plane that coincides with the edges on the element-side of the one or more submounts and that is parallel to the first inner lateral surface.

18. The light emitting device according to claim 1, wherein the semiconductor laser elements include a first semiconductor laser element arranged at a position closest to the second inner lateral surface among the semiconductor laser elements, the second wire is bonded to the upper surface of the frame part in the first region on the element-side of the first semiconductor laser element, at least a part of the first protective element is arranged in the first region on the element-side of the first semiconductor laser element, and the first wire is bonded to the upper surface of the frame part in the first region at a position between the plane that coincides with the edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface and the plane that coincides with the edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface.

19. The light emitting device according to claim 1, wherein the semiconductor laser elements include a first semiconductor laser element arranged at a position closest to the second inner lateral surface among the semiconductor laser elements, the second wire is bonded to the upper surface of the frame part in the first region on the element-side of the first semiconductor laser element, at least a part of the first protective element is arranged in the first region at a position between a plane that coincides with an edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface and a plane that coincides with an edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface, and the first wire is bonded to the upper surface of the frame part in the first region at a position between the plane that coincides with the edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface and the plane that coincides with the edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface.

20. The light emitting device according to claim 10, wherein the semiconductor laser elements include a first semiconductor laser element arranged at a position closest to the second inner lateral surface among the semiconductor laser elements, the second wire is bonded to the upper surface of the frame part in the first region on the element-side of the first semiconductor laser element, at least a part of the first protective element is arranged in the first region at a position between a

plane that coincides with an edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface and a plane that coincides with an edge on the element-side of one of the one or more submounts on which the first semiconductor laser element is mounted and that is parallel to the first inner lateral surface, and the first wire is bonded to the upper surface of the frame part in the first region at a position between a plane that coincides with an edge on the light traveling side of the first semiconductor laser element and that is parallel to the first inner lateral surface and the plane that coincides with the edge on the element-side of the first semiconductor laser element and that is parallel to the first inner lateral surface.
